

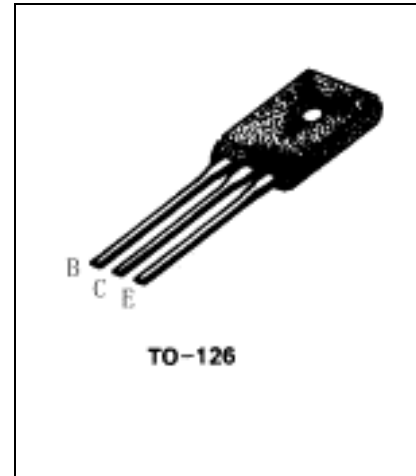
NPN SILICON POWER TRANSISTOR**BUL6802**

● **FEATURES:** ■ HIGH VOLTAGE CAPABILITY ■ HIGH SWITCHING SPEED ■ WIDE SOA

● **APPLICATIONS:** ■ ELECTRONIC BALLASTS FOR FLUORESCENT LIGHTING
■ COMPACT FLUORESCENT LAMP

● **MAXIMUM RATINGS ($T_c=25^\circ\text{C}$) TO-126**

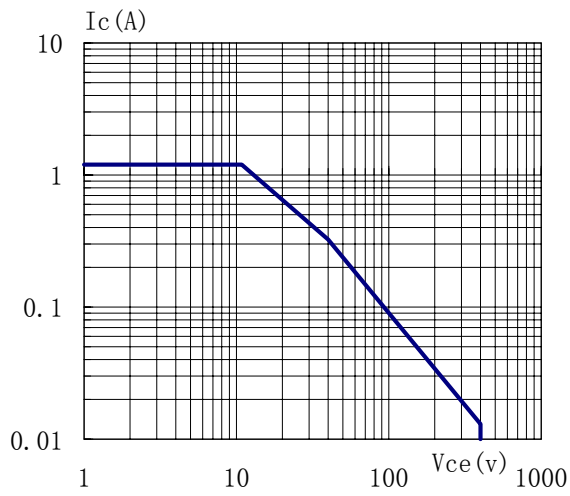
PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	600	V
Collector-Emitter Voltage	V_{CEO}	400	V
Emitter-Base Voltage	V_{EBO}	9	V
Collector Current	I_C	1.2	A
Total Power Dissipation	P_C	25	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-65-150	$^\circ\text{C}$



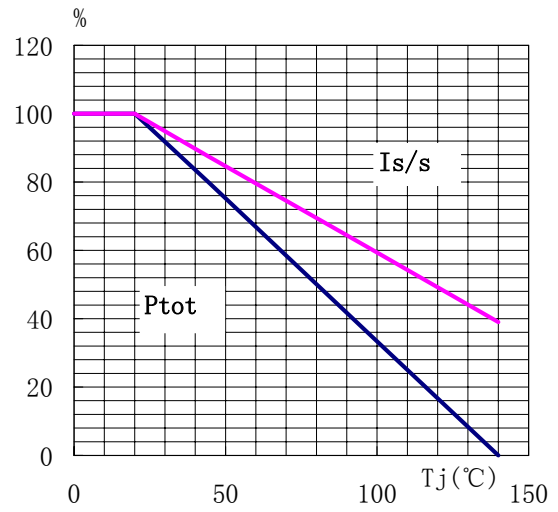
● **ELECTRICAL CHARACTERISTICS ($T_c=25^\circ\text{C}$)**

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	MAX	UNIT
Collector Cutoff Current	I_{CBO}	$V_{CB}=600\text{V}$		100	μA
Collector Cutoff Current	I_{CEO}	$V_{CE}=400\text{V}, I_B=0$		250	μA
Collector-Emitter Sustaining Voltage	V_{CEO}	$I_C=10\text{mA}, I_B=0$	400		V
Base-Emitter Sustaining Voltage	V_{EBO}	$I_E=1\text{mA}, I_C=0$	9		V
Collector-Emitter Saturation Voltage	V_{ces}	$I_C=0.2\text{A}, I_B=0.04\text{A}$		0.5	V
		$I_C=0.5\text{A}, I_B=0.1\text{A}$		1.0	
		$I_C=1.0\text{A}, I_B=0.2\text{A}$		3	
Base-Emitter Saturation Voltage	V_{bes}	$I_C=0.5\text{A}, I_B=0.1\text{A}$		1.2	V
DC Current Gain	h_{FE}	$V_{CE}=5\text{V}, I_C=5\text{mA}$	8		
		$V_{CE}=5\text{V}, I_C=0.2\text{A}$	10	40	
		$V_{CE}=5\text{V}, I_C=0.6\text{A}$	8		
Storage Time	t_s	$V_{CC}=250\text{V}, I_C=5I_B, I_{B1}=I_{B2}=0.1\text{A}$		3.0	μS
Fall Time	t_f			0.8	

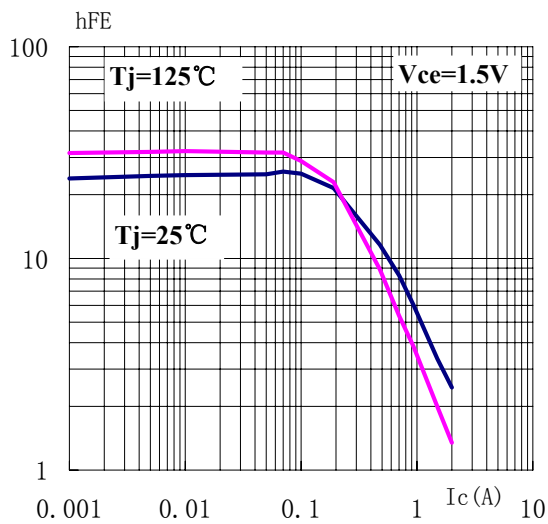
SOA(DC)



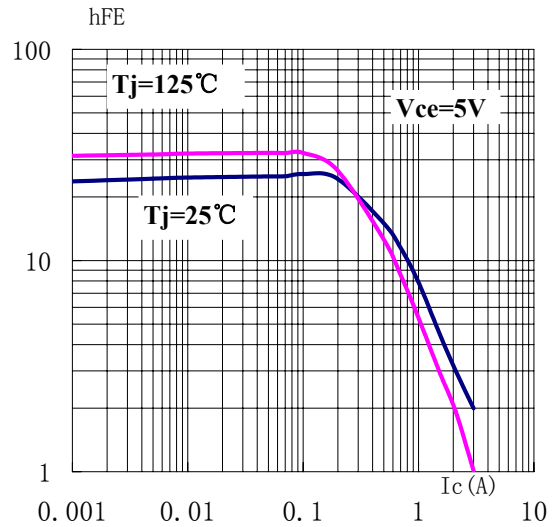
$Pc \propto Tj$



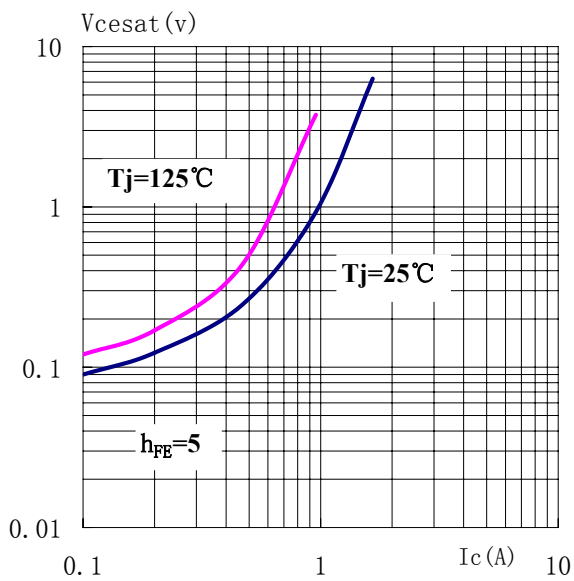
hFE-Ic



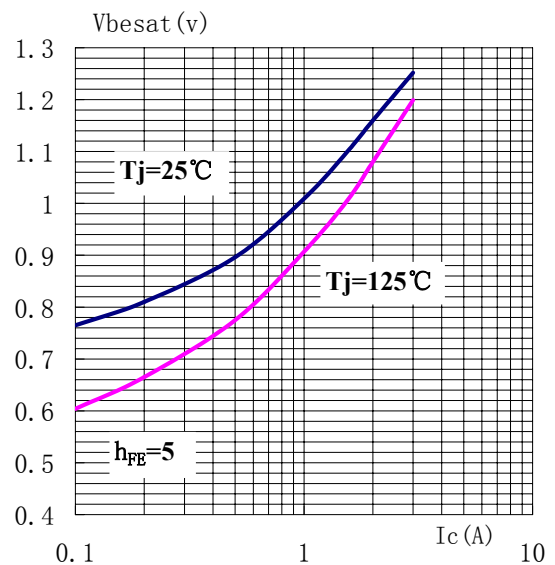
hFE-Ic



Vcesat-Ic



Vbesat-Ic



TO-126 MECHANICAL DATA

UNIT: mm

SYMBOL	min	nom	max	SYMBOL	min	nom	max
A	2.3		2.8	L	15.3		16.5
B	1.0		1.2	L1			2.54
B1	0.8		1.0	ϕP	3.0		3.2
b	0.65		0.88	$\phi P1$		5.0	
c	0.45		0.60	Q	3.6		4.4
D	10.5		11.1	Q1	0.9		1.5
E	7.2		7.8	R		0.5*	
e		2.29					

